

SUPERCONDUCTIVITY IN  $\text{CeRh}_2\text{Si}_2$   
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We have studied the pressure-induced superconductivity in an antiferromagnet  $\text{CeRh}_2\text{Si}_2$  by measuring the electrical resistivity for a high-quality single crystal. The superconducting resistivity drop was observed around  $P_c \simeq 1.06$  GPa, at which the Néel temperature becomes zero, namely in a pressure region from 0.97 to 1.20 GPa. The zero resistivity appears below 0.4 K between 1.03 to 1.08 GPa. The resistivity at low temperatures follows the Fermi liquid  $AT^2$  relation in the whole pressure region, even at  $P_c$ . The  $A$  value becomes a maximum around  $P_c$ .

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In some antiferromagnetic cerium compounds, the Néel temperature  $T_N$  decreases with increasing pressure and vanishes at  $P_c$ . The superconductivity around  $P_c$  has been reported in a few compounds such as  $\text{CePd}_2\text{Si}_2$  and  $\text{CeIn}_3$  [1].

$\text{CeRh}_2\text{Si}_2$  is one of the pressure-induced superconductor [2], which crystallizes in the tetragonal  $\text{ThCr}_2\text{Si}_2$ -type structure.  $\text{CeRh}_2\text{Si}_2$  is an antiferromagnet with  $T_N = 36$  K at ambient pressure.  $T_N$  decreases monotonously

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with increasing pressure and vanishes at  $P_c \simeq 1.06$  GPa. Superconductivity with  $T_{sc} = 0.35$  K was found by Movshovich *et al.* [2] for a polycrystalline sample, in which superconductivity appears in a relatively wide pressure range from 0.6 to 1.6 GPa around  $P_c$ .

We searched for superconductivity in a single crystal with the residual resistivity ratio  $RRR \simeq 30$ , but no evidence of superconductivity was observed. On the other hand, the superconducting resistivity drop was observed below  $T_{sc}$  for a polycrystalline sample with  $RRR = 62$  in the pressure range from 0.7 to 2.9 GPa [3]. The  $T_{sc}$  value was unchanged in this pressure range, but the degree of the resistivity drop had a maximum around  $P_c$ . Recently, we have succeeded in growing a high-quality single crystal with  $RRR = 100$ . The superconducting resistivity drop in the sample was observed at 1.1 GPa, where  $T_{sc} = 0.38$  K but the resistivity remains a finite value even at 35 mK [4]. We continued the investigation of superconductivity for the high-quality single crystalline sample.

Single crystals of  $\text{CeRh}_2\text{Si}_2$  were grown by the Czochralski pulling method in a tetra-arc furnace. Starting materials were 4N (99.99% pure)-Ce, 4N-Rh and 5N-Si. The electrical resistivity was measured by a four-probe ac resistance bridge (Linear Research, LR-700) at low temperatures down to about 100 mK with a dilution refrigerator. The current was directed along the [001] direction. Pressures were applied by utilizing a BeCu piston-cylinder cell with a 1:1 mixture of commercial Daphne oil (7373) and kerosene as a pressure-transmitting medium.

The low-temperature electrical resistivity under pressures follows the Fermi liquid relation  $\rho = \rho_0 + AT^2$ . Fig. 1 shows the pressure dependence of the  $A$  and  $\rho_0$  values. With applying pressures,  $A$  value increases and shows a maximum around 1.0 GPa.  $\sqrt{A}$  (1 GPa)/ $\sqrt{A}$  (0 GPa) = 3.8 is consistent with the ratio of the electronic specific heat coefficient  $\gamma$  (1 GPa)/ $\gamma$  (0 GPa)  $\simeq 3.5$  [5]. The residual resistivity  $\rho_0$  has an anomaly around 1.0 GPa.

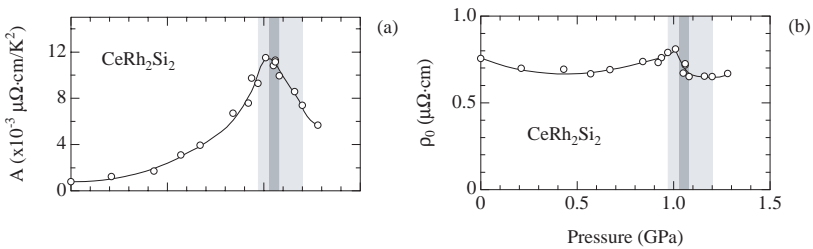


Fig. 1. Pressure dependence of  $A$  and  $\rho_0$  values in  $\text{CeRh}_2\text{Si}_2$ .

Superconductivity appears around  $P_c$ , as shown in Fig. 2. An indication of superconductivity appears in the pressure region from 0.97 to 1.20 GPa, which is shown in Fig. 1 as a gray region. As shown in Fig. 2, the resistivity

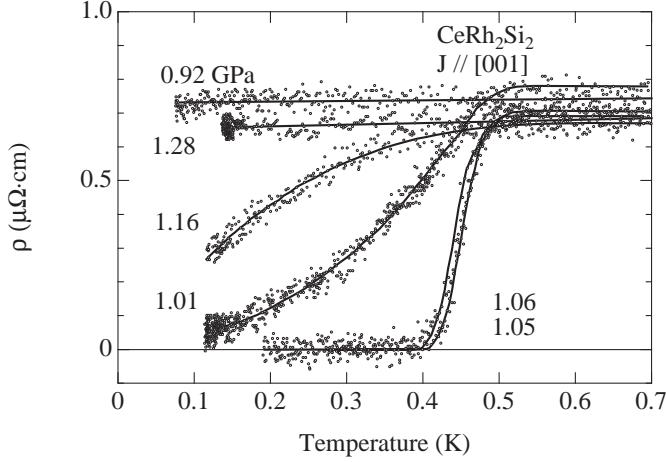


Fig. 2. Superconducting transition in the resistivity measurements in  $\text{CeRh}_2\text{Si}_2$ .

at  $P = 1.01$  and  $1.16$  GPa decreases gradually with decreasing temperature below  $0.5$  K, but the zero resistivity is not attained. The zero resistivity is observed in an extremely narrow pressure region around  $P_c$  from  $1.05$  to  $1.08$  GPa, which is shown in Fig. 1 as a dense-gray region.

We also determined the upper critical field  $H_{c2}$  in superconductivity. Fig. 3(a) shows the temperature dependence of the electrical resistivity under magnetic fields along the  $[001]$  direction. The superconducting temperature  $T_{sc}$  for each field is defined as the temperature obtained from the extrapolation of the resistivity drop, as shown at  $0$  T in Fig. 3(a). Fig. 3(b) shows the temperature dependence of  $H_{c2}$ . A solid line in Fig. 3(b) is a guide to eyes. The coherence length  $\xi$  is estimated as  $340 \text{ \AA}$  from  $H_{c2}(0)$  ( $= \Phi_0/2\pi\xi^2$ ),

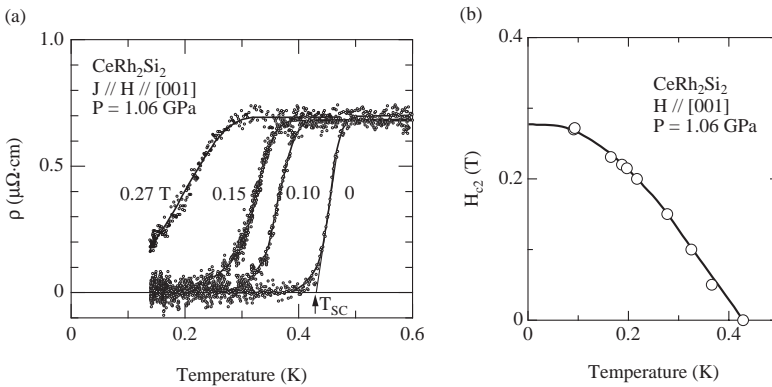


Fig. 3. (a) Low-temperature resistivity under magnetic fields and (b) temperature dependence of  $H_{c2}$  at  $1.06$  GPa in  $\text{CeRh}_2\text{Si}_2$ .

where  $\Phi_0$  is the quantum flux. We note that the mean free path for the present sample around 1.06 GPa is estimated from the de Haas–van Alphen experiment, being about 1000 Å. This indicates that the present sample is close to a clean limit.

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